

Description

The SIRA12DP-T1-GE3 uses advanced trench technology

to provide excellent $R_{DS(ON)}$, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

 $V_{DS} = 30V I_{D} = 120A$

 $R_{DS(ON)} < 4.4 \text{mÙ V}_{GS} = 10 \text{V}$

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

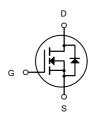
Product ID	Pack	Brand	Qty(PCS)
SIRA12DP-T1-GE3	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	120	А
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	66	А
Ірм	Pulsed Drain Current ²	320	А
EAS	Single Pulse Avalanche Energy ³	180	mJ
las	Avalanche Current	60	А
P _D @T _C =25°C	Total Power Dissipation ⁴	187	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R _θ JA	Thermal Resistance Junction-Ambient ¹	62	°C/W
ReJC	Thermal Resistance Junction-Case ¹	1.1	°C/W



DFN5X6-8L



N-Channel MOSFET



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVpss	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
2BV DSS/ 2T J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.014		V/°C
		V _{GS} =10V , I _D =30A		3.5	4.4	
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =15A		4.6	5.8	$\mathbf{m}\Omega$
V _{GS(th)}	Gate Threshold Voltage	,	1.2		2.5	V
${\Bbb P}V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	 V _{GS} =V _{DS} , I _D =250uA		-4		mV/°C
		V _{DS} =24V , V _{GS} =0V , T _J =25°C			1	
IDSS	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =55°C			5	uA
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =30A		50		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			56.9		
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =10V , I _D =15A		13.8		nC
Qgd	Gate-Drain Charge	_		23.5		
Td(on)	Turn-On Delay Time			20.1		
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		6.3		
Td(off)	Turn-Off Delay Time	—R _G =3.3 , I _D =1A		124.6		ns
T _f	Fall Time			15.8		
Ciss	Input Capacitance			4345		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		340		pF
Crss	Reverse Transfer Capacitance	1		225		
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			85	Α
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V

Typical Characteristics

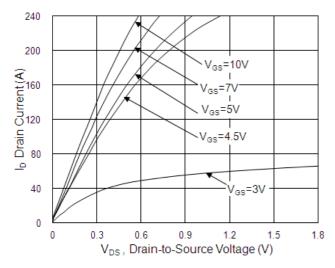


Fig.1 Typical Output Characteristics

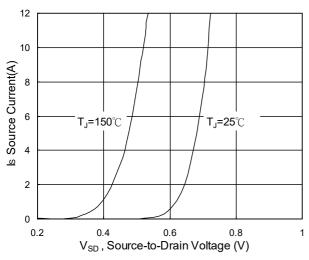


Fig.3 Forward Characteristics of Reverse

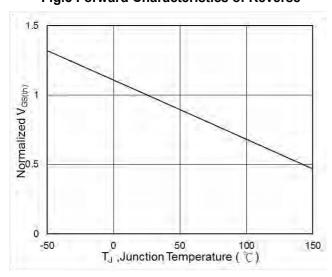


Fig.5 Normalized $V_{\text{GS(th)}}$ v.s T_{J}

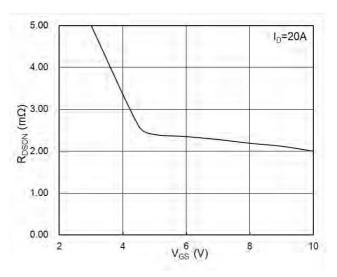


Fig.2 On-Resistance v.s Gate-Source

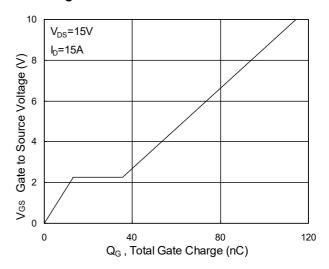


Fig.4 Gate-Charge Characteristics

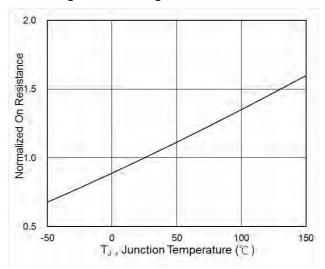


Fig.6 Normalized R_{DSON} v.s T_J

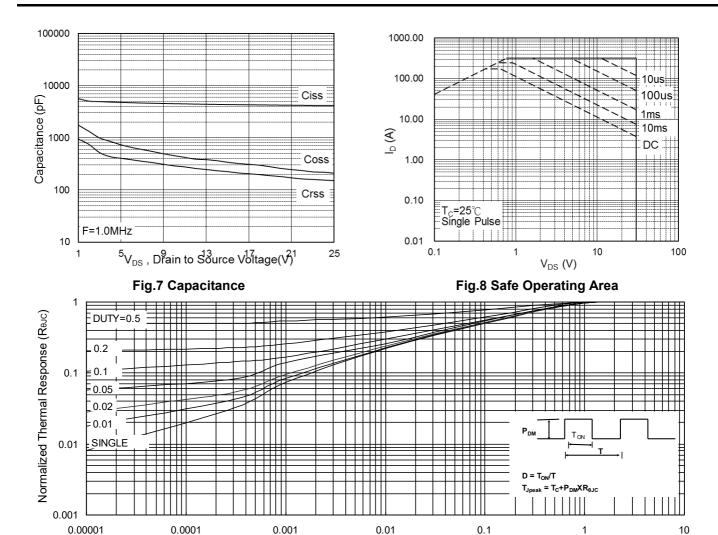


Fig.9 Normalized Maximum Transient Thermal Impedance

t, Pulse Width (s)

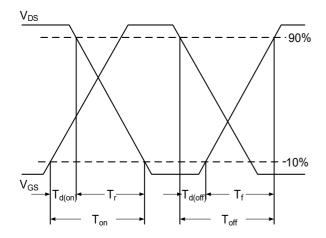


Fig.10 Switching Time Waveform

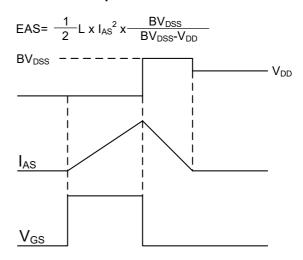
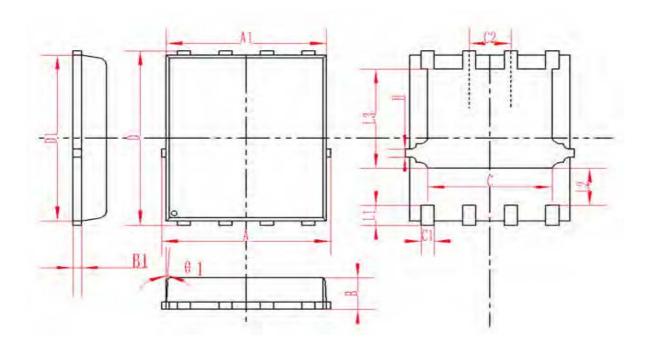


Fig.11 Unclamped Inductive Switching Waveform



DFN5X6-8L Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1		0.254REF			0.010REF	
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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